



# SSF2318E

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## Thermal Resistance

Symbol	Characterizes	Typ.	Max.	Units
$R_A$	Junction-to-Ambient		90	/W

## Electrical Characterizes @ $T_A=25$ unless otherwise specified

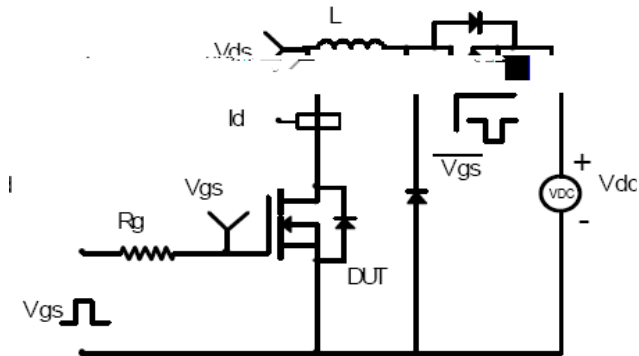
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	20			V	$V_{GS} = 0V, I_D$
$R_{DS(on)}$	Static Drain-to-Source on-resistance		18	22	m	$V_{GS}=4.5V, I_D=6.5A$
			24	30	m	$V_{GS}=2.5V, I_D=5.5A$
$V_{GS(th)}$	Gate threshold voltage	0.4		1	V	$V_{DS} = V_{GS}, I_D$
$I_{DSS}$	Drain-to-Source leakage current			1		$V_{DS}=20V, V_{GS}=0V$
$I_{GSS}$	Gate-to-Source forward leakage			$\pm 1$	uA	$V_{GS}=\pm 4.5V, V_{DS}=0V$
				$\pm 10$		$V_{GS}=\pm 8V, V_{DS}=0V$
$Q_g$	Total gate charge		10		nC	$V_{DS}=10V$
$Q_{gs}$	Gate-to-Source charge		2.3			$I_D=6.5A$
$Q_{gd}$	Gate-to-Drain("Miller") charge		3			$V_{GS}=4.5V$
$t_{d(on)}$	Turn-on delay time		6.5		ns	$V_{DD}=10V$
$t_r$	Rise time		13			$I_D=1A$
$t_{d(off)}$	Turn-Off delay time		50			$V_{GS}=5V$
$t_f$	Fall time		30			$R_{GEN}$
$C_{iss}$	Input capacitance		1160		pF	$V_{GS} = 0V$
$C_{oss}$	Output capacitance		200			$V_{DS} = 10V$
$C_{riss}$	Reverse transfer capacitance		140			1MHz

## Source-Drain Ratings and Characteristics

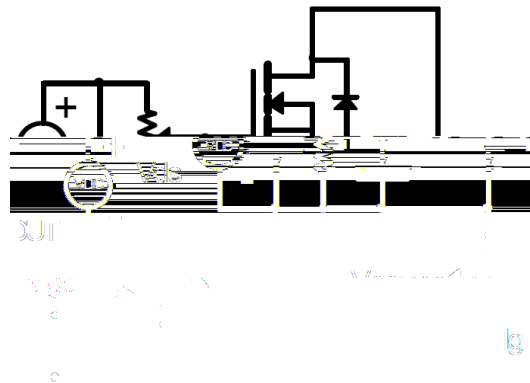
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)			6.5	A	MOSFET symbol

## Test Circuits and Waveforms

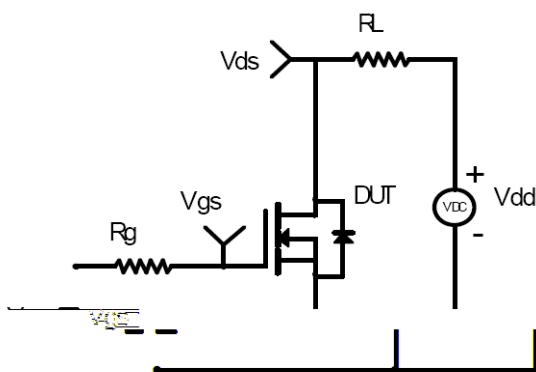
EAS Test Circuit:



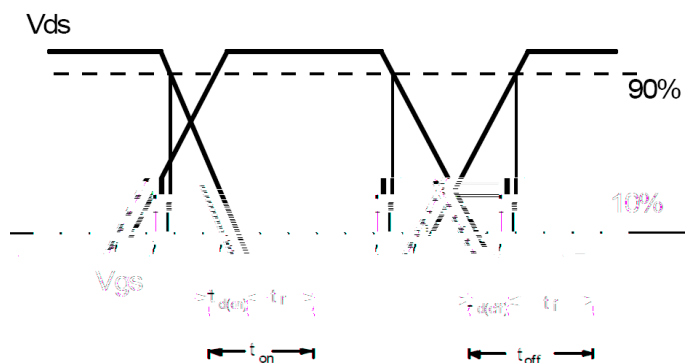
Gate Charge Test Circuit:



Switching Time Test Circuit:



Switching Waveforms:



## Notes:

Calculated continuous current based on maximum allowable junction temperature.

Repetitive rating; pulse width limited by max. junction temperature.

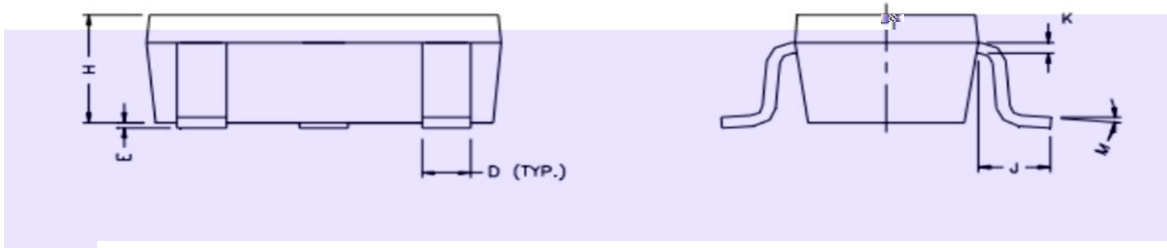
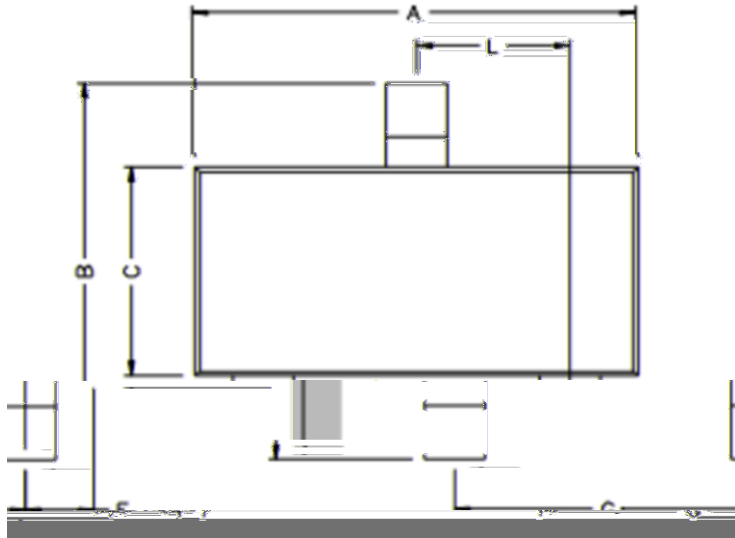
The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.

The value of  $R_A$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25$



Mechanical Data

SOT-23 Package Outline(Unit:mm)



REF.	Millimeter		REF.	Millimete	
	Min.	Max.		Min.	Max.
A	2.80	3.00	G	1.80	2.00
B	2.30	2.50	H	0.90	1.1
C	1.20	1.40	K	0.10	0.20
D	0.30	0.50	J	0.35	0.70
E	0	0.10	L	0.92	0.98
F	0.45	0.55	M	0°	10°

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